Wafer Marking System



Small footprint.

Features

This system is for marking on wafers; silicon wafer, sapphire substrate, and compound wafer.

- Small footprint.
- Highly precise marking.
- High throughput.

[White marking: by SHG laser]

It melts only surface of a silicon wafer, so marking can be done without particles.

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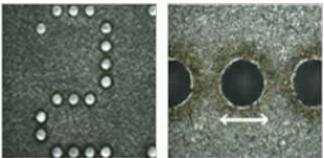
Φ70μm in diameter, 2.5μm in deep





[Black marking: by fundamental laser]

It engraves surface of a silicon wafer. Marked workpiece has a high level of visibility and can be read clearly even after cleansing and grinding.



Φ60μm in diameter, 100μm in deep



Inside of the system

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Control display





Specifications

Wafer size	4, 5, 6, 8 inch, and 12 inch*			
Marking	Soft / hard marking			
Marking positioning accuracy	+/- 200µm (Option: +/- 75µm)			
Takt time	150WPH (5x9 dots, 12 letters)			

*For 12 inch (Two cassettes FOUP)



